

Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
30	0.022 at $V_{GS} = 10$ V	7.5
	0.030 at $V_{GS} = 4.5$ V	6.5

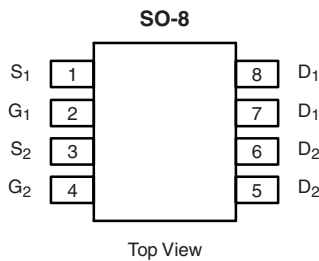
SCHOTTKY PRODUCT SUMMARY		
V_{DS} (V)	V_{SD} (V) Diode Forward Voltage	I_F (A)
30	0.50 V at 1.0 A	2.0

FEATURES

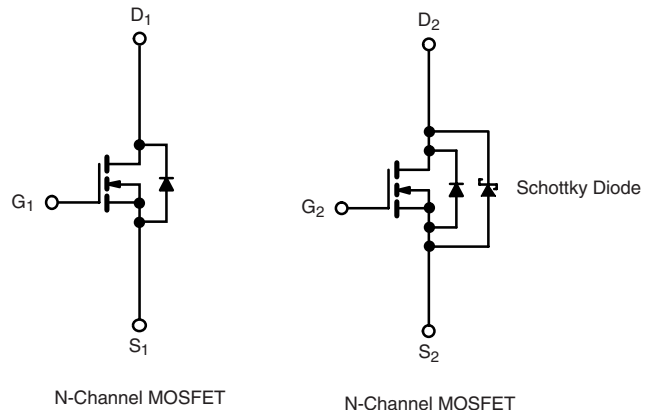
- Halogen-free According to IEC 61249-2-21 Definition
- LITTLE FOOT® Plus
- Compliant to RoHS directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



Ordering Information: Si4808DY-T1-E3 (Lead (Pb)-free)
Si4808DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	30		V
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	7.5	5.7
		$T_A = 70$ °C	6.0	4.6
Pulsed Drain Current	I_{DM}	30		A
Continuous Source Current (Diode Conduction) ^a	I_S	1.7	0.9	
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	2.0	1.1
		$T_A = 70$ °C	1.3	0.7
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	MOSFET		Schottky		Unit
		Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	52	62.5	53	62.5
		Steady-State	93	110	93	110
Maximum Junction-to-Foot (Drain)	R_{thJC}	35	40	35	40	°C/W

Notes:
a. Surface Mounted on 1" x 1" FR4 board.

MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.8			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 20\ \text{V}$			± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24\ \text{V}, V_{GS} = 0\ \text{V}$	Ch-1		1	μA	
			Ch-2		100		
		$V_{DS} = 24\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 85\text{ }^\circ\text{C}$	Ch-1		15		
			Ch-2		2000		
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\ \text{V}, V_{GS} = 10\ \text{V}$	20			A	
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\ \text{V}, I_D = 7.5\ \text{A}$		0.018	0.022	Ω	
		$V_{GS} = 4.5\ \text{V}, I_D = 6.5\ \text{A}$		0.024	0.030		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\ \text{V}, I_D = 7.5\ \text{A}$		22		S	
Diode Forward Voltage ^b	V_{SD}	$I_S = 1\ \text{A}, V_{GS} = 0\ \text{V}$	Ch-1		0.8	1.2	V
			Ch-2		0.47	0.5	
Dynamic^a							
Total Gate Charge	Q_g	$V_{DS} = 15\ \text{V}, V_{GS} = 10\ \text{V}, I_D = 7.5\ \text{A}$		13	20	nC	
Gate-Source Charge	Q_{gs}			2			
Gate-Drain Charge	Q_{gd}			2.7			
Gate Resistance	R_g		0.5		3.2	Ω	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}, R_L = 15\ \Omega$ $I_D \cong 1\ \text{A}, V_{GEN} = 10\ \text{V}, R_g = 6\ \Omega$		8	16	ns	
Rise Time	t_r			10	20		
Turn-Off Delay Time	$t_{d(off)}$			21	40		
Fall Time	t_f			10	20		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$	Ch-1		40	80	
			Ch-2		32	70	

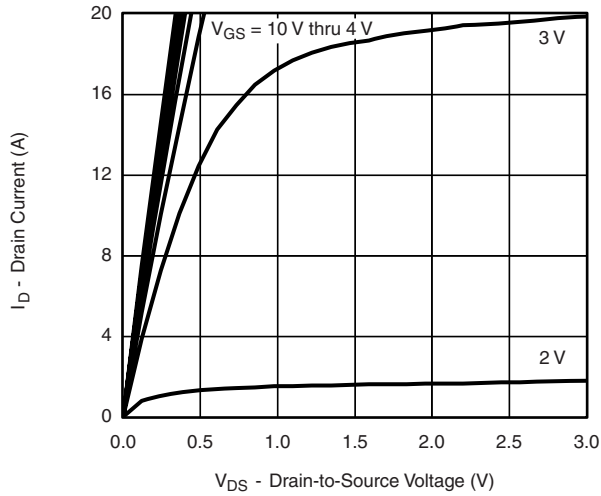
Notes:

- a. Guaranteed by design, not subject to production testing.
 b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

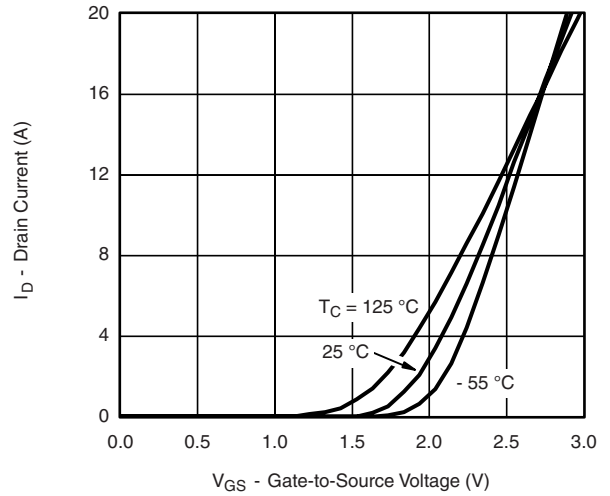
SCHOTTKY SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage Drop	V_F	$I_F = 1.0\ \text{A}$		0.47	0.50	V
		$I_F = 1.0\ \text{A}, T_J = 125\text{ }^\circ\text{C}$		0.36	0.42	
Maximum Reverse Leakage Current	I_{rm}	$V_R = 30\ \text{V}$		0.004	0.100	mA
		$V_R = 30\ \text{V}, T_J = 100\text{ }^\circ\text{C}$		0.7	10	
		$V_R = -30\ \text{V}, T_J = 125\text{ }^\circ\text{C}$		3.0	20	
Junction Capacitance	C_T	$V_R = 10\ \text{V}$		50		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

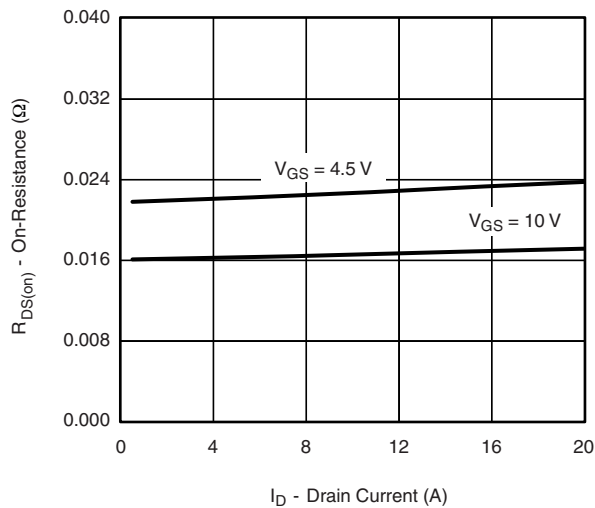
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



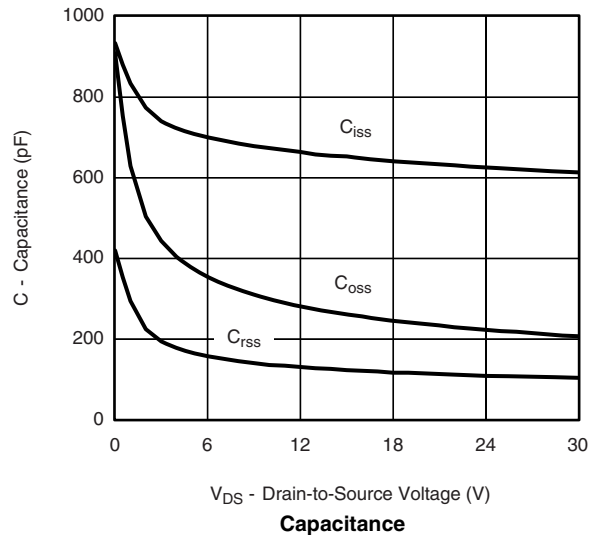
Output Characteristics



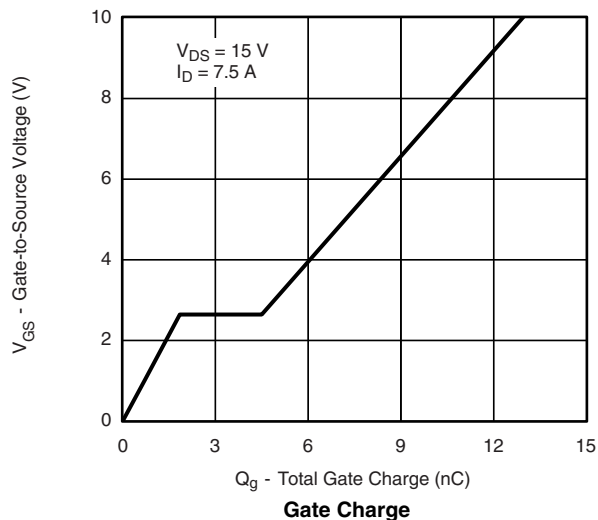
Transfer Characteristics



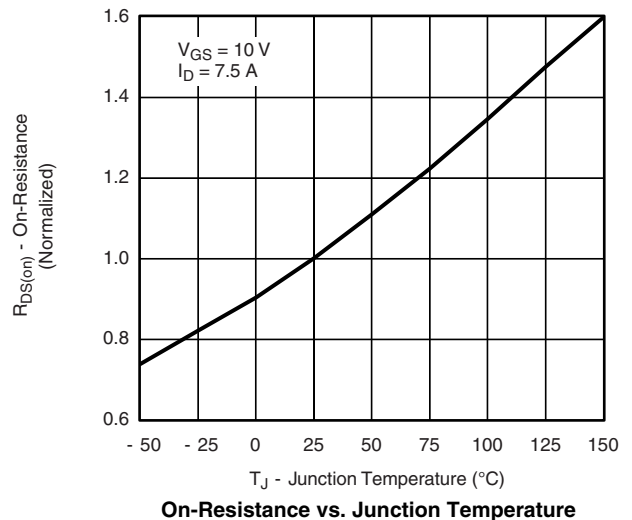
On-Resistance vs. Drain Current



Capacitance

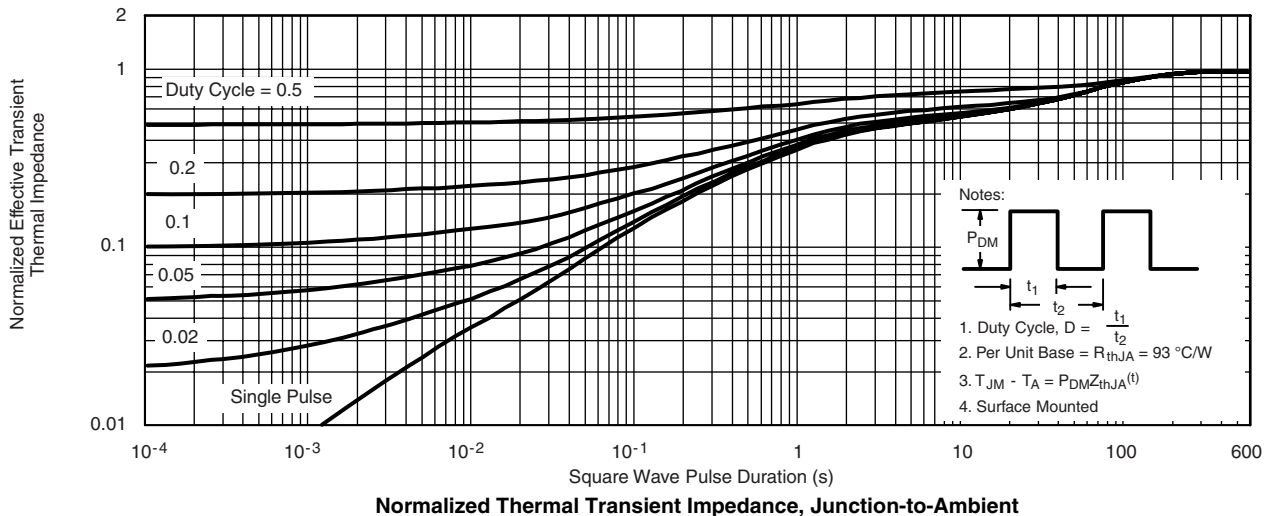
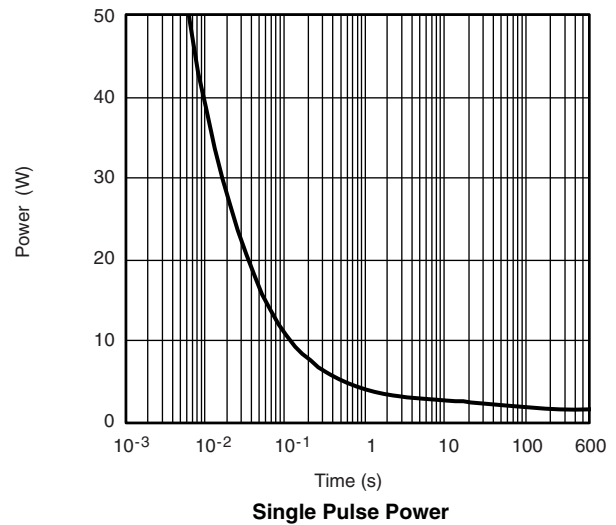
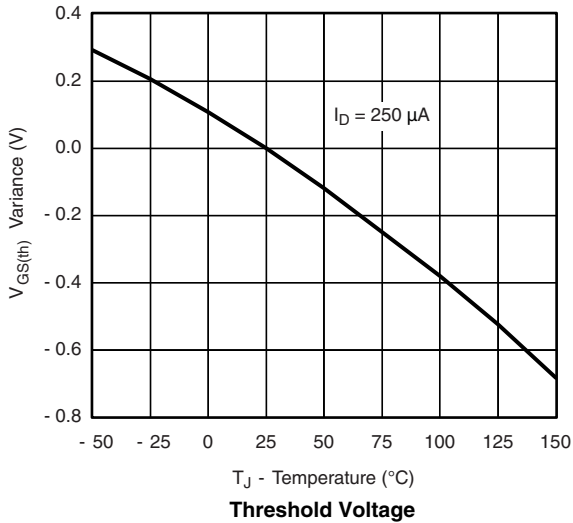
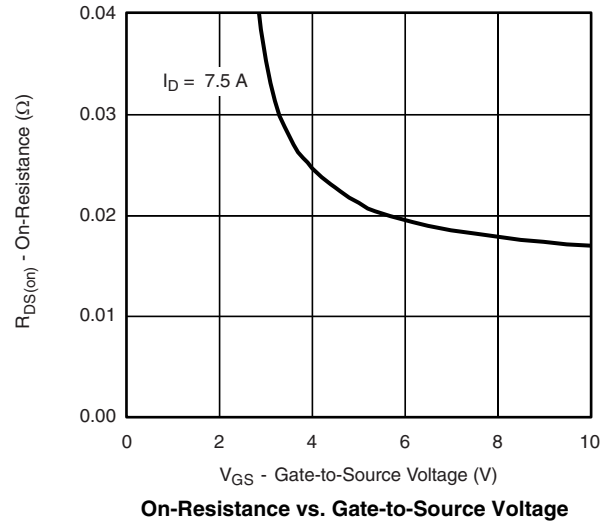
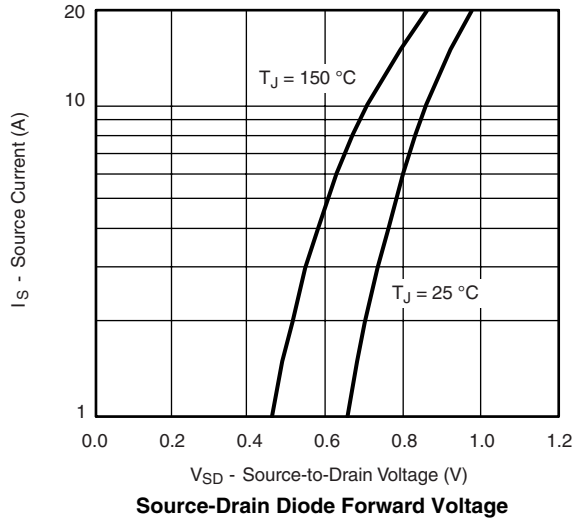


Gate Charge

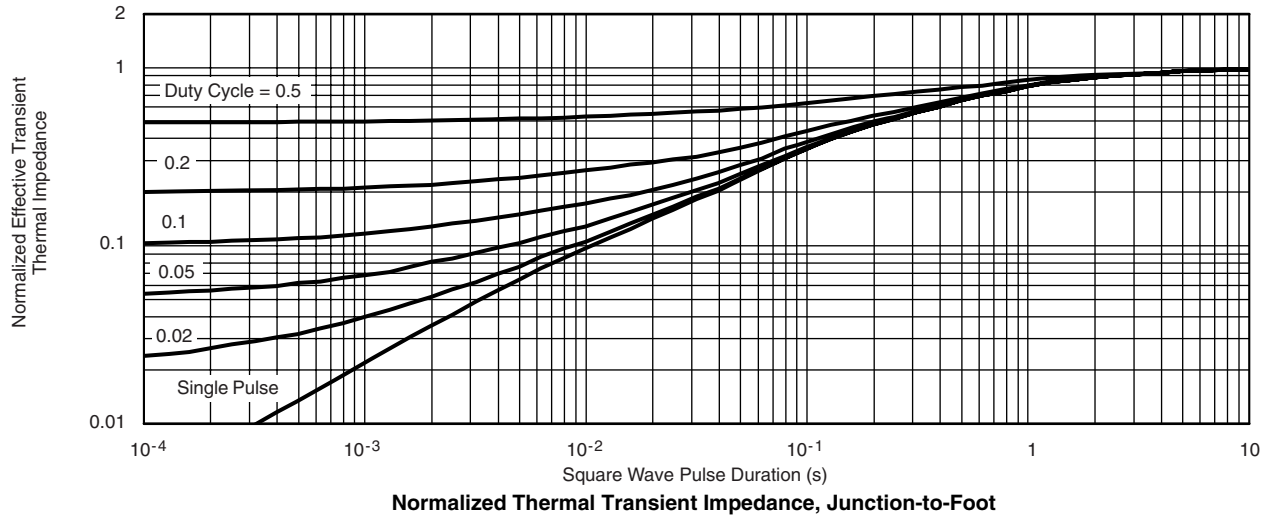


On-Resistance vs. Junction Temperature

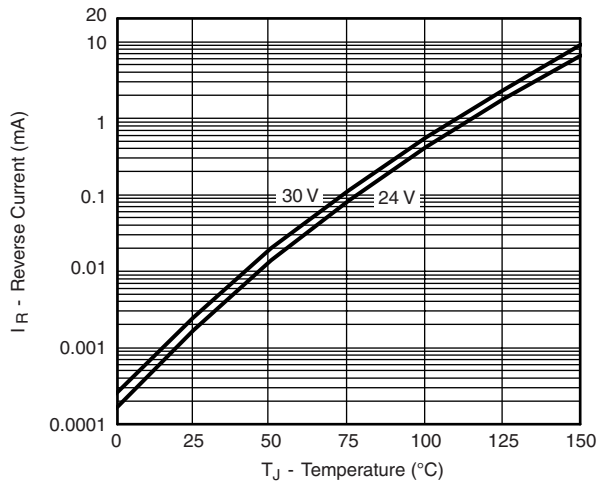
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



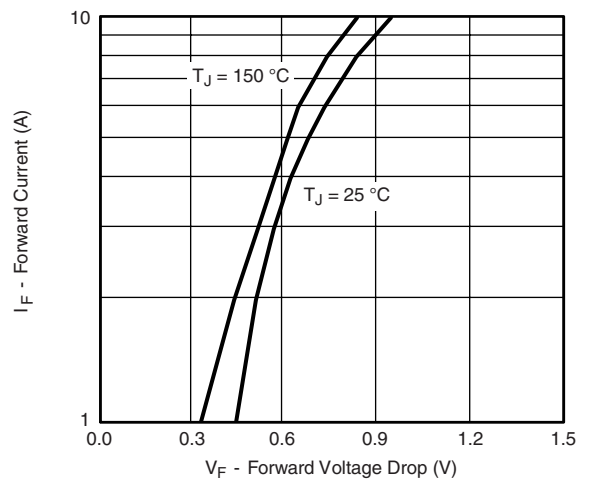
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



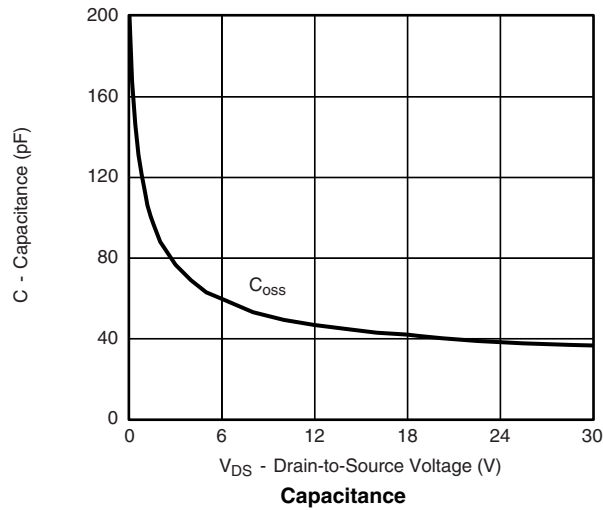
SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Reverse Current vs. Junction Temperature



Forward Voltage Drop



Capacitance

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